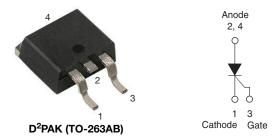
Vishay Semiconductors

# **Thyristor Surface Mount, Phase Control SCR, 8 A**



8 A

800 V

1.2 V

15 mA

-40 to +125 °C

D<sup>2</sup>PAK (TO-263AB)

Single SCR

**PRIMARY CHARACTERISTICS** 

I<sub>T(AV)</sub>

V<sub>DRM</sub>/V<sub>RRM</sub>

V<sub>TM</sub>

ΤJ

Package

Circuit configuration

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F	E	Δ	т	U	R	E	S
		~		J			-

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

### DESCRIPTION

The VS-12TTS08SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS						
Capacitive input filter $T_A = 55 \text{ °C}$ , $T_J = 125 \text{ °C}$ , common heatsink of 1 °C/W	13.5	17	A						

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	8	Α.						
I <sub>T(RMS)</sub>		12.5	~						
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V						
I <sub>TSM</sub>		110	A						
V <sub>T</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V						
dV/dt		150	V/µs						
dl/dt		100	A/µs						
TJ	Range	-40 to +125	°C						

VOLTAGE RATINGS										
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> AT 125 °C mA							
VS-12TTS08SLHM3	800	800	5.0							

Revision: 22-Feb-18 Document Number: 96121 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



COMPLIANT HALOGEN

## VS-12TTS08SLHM3



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ABSOLUTE MAXIMUM RATINGS	;			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$T_{\rm C}$ = 108 °C, 180° conduction, half sine wave	8	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	$T_{\rm C} = 100$ C, 100 conduction, that sine wave	12.5	А
Maximum peak one-cycle	<b>L</b>	10 ms sine pulse, rated $V_{RRM}$ applied, $T_{J}$ = 125 $^{\circ}\text{C}$	95	A
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied, $T_J$ = 125 °C	110	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J$ = 125 °C	45	A <sup>2</sup> s
	1-1	10 ms sine pulse, no voltage reapplied, $T_J$ = 125 °C	64	A-2
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, $T_{J}$ = 125 $^{\circ}\text{C}$	640	A²√s
Maximum on-state voltage drop	V <sub>TM</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V
On-state slope resistance	r <sub>t</sub>	T.I = 125 °C	16.2	mΩ
Threshold voltage	V <sub>T(TO)</sub>	11 - 123 0	0.87	V
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$T_J = 25 \degree C$ $V_B = rated V_{BBM} / V_{DBM}$	0.05	
Maximum reverse and direct leakage current	'RM' 'DM	$T_J = 125 \text{ °C}$	5.0	
Typical holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C	30	mA
Typical latching current	١L	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$ , linear to 80 %, $V_{DRM} = R_g - k = open$	150	V/µs
Maximum rate of rise of turned-on current	dl/dt		100	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv	
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	А	
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, $T_J = -65 \degree C$ GTAnode supply = 6 V, resistive load, $T_J = 25 \degree C$		mA	
Maximum required DC gate current to trigger	I <sub>GT</sub>				
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	10		
		Anode supply = 6 V, resistive load, $T_J$ = -65 °C	1.2		
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	1		
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	0.7	V	
Maximum DC gate voltage not to trigger	V <sub>GD</sub>		0.2		
Maximum DC gate current not to trigger	I <sub>GD</sub>	$T_J = 125 \text{ °C}, V_{DRM} = \text{rated value}$	0.1	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	3	μs
Typical turn-off time	t <sub>q</sub>	1j = 125°C	100	

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THERMAL AND MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C						
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5							
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>		62	°C/W						
Typical thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.5							
Approximate weight			2	g						
			0.07	oz.						
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	12TTS	S08SH						

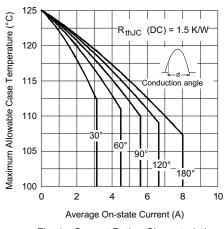
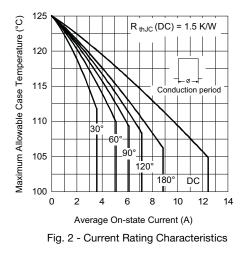


Fig. 1 - Current Rating Characteristics



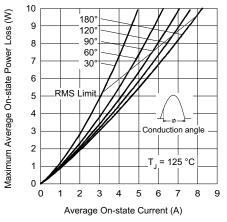


Fig. 3 - On-State Power Loss Characteristics

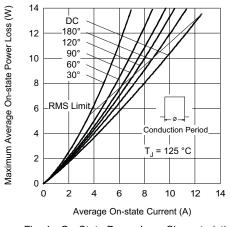
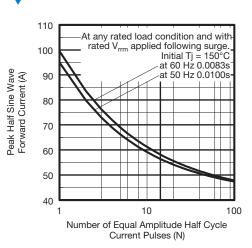


Fig. 4 - On-State Power Loss Characteristics

## VS-12TTS08SLHM3

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Fig. 5 - Maximum Non-Repetitive Surge Current

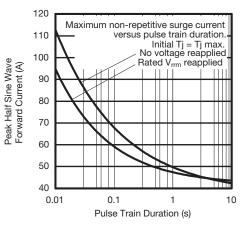


Fig. 6 - Maximum Non-Repetitive Surge Current

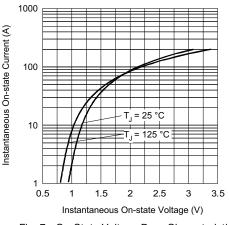


Fig. 7 - On-State Voltage Drop Characteristics

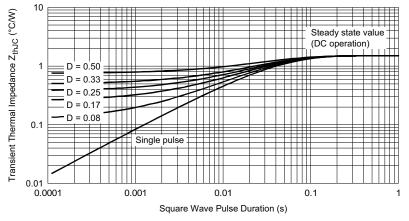


Fig. 8 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

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**ORDERING INFORMATION TABLE** 

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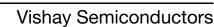
ISHA

Device code	VS-	12	т	т	s	08	S	L	н	М3
		2	3	4	5	6	7	8	9	10
	<ol> <li>Vishay Semiconductors product</li> <li>Current rating (12.5 A)</li> <li>Circuit configuration: T = single thyristor</li> <li>Package: T = D<sup>2</sup>PAK (TO-263AB)</li> <li>Type of silicon:</li> </ol>									
	6 - 7 - 8 - 9 - 10 -	Voli S = L = H = Env	tage rati surface tape an AEC-Q rironmer	101 qua ntal digit	= 800 V) Ible eft orien Ilified :	ted), foi				ontact fa ad (Pb)-f

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-12TTS08SLHM3	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95444						
Packaging information	www.vishay.com/doc?96317						

## **Outline Dimensions**

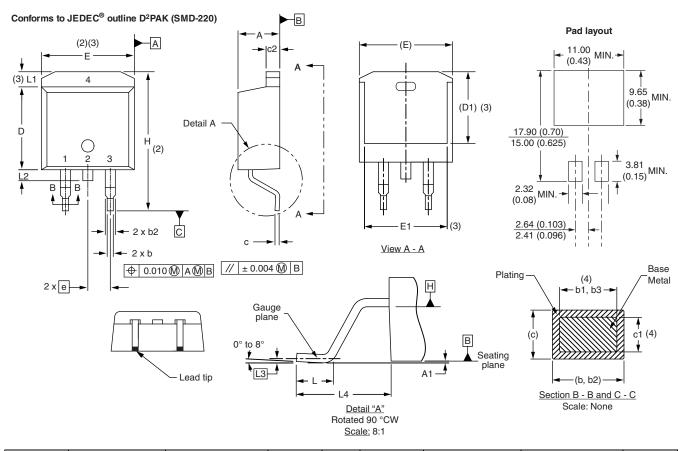


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D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches

SHA



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SVMBOL		SYMBOL		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	) BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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